



FTD2017R — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 2.5V drive.
- Mount height 1.1mm.
- Composite type, facilitating high-density mounting.
- Drain common specifications.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1000mm ² ×0.8mm)1unit	1.2	W
Total Dissipation	P _T	Mounted on a ceramic board (1000mm ² ×0.8mm)	1.25	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =6A	6.9	11.5		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =6A, V _{GS} =4.5V	11	17	23	mΩ
	R _{DS(on)2}	I _D =6A, V _{GS} =4V	12	18	24	mΩ
	R _{DS(on)3}	I _D =3A, V _{GS} =3.1V	14	19	30	mΩ
	R _{DS(on)4}	I _D =3A, V _{GS} =2.5V	14.4	20	33	mΩ

Marking : D2017R

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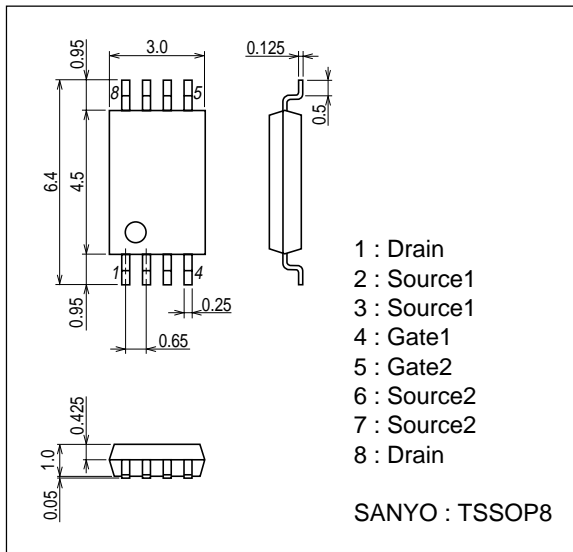
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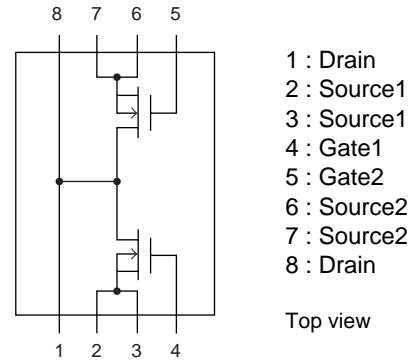
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		960		ns
Rise Time	t_r	See specified Test Circuit.		2700		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		5500		ns
Fall Time	t_f	See specified Test Circuit.		5400		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		10		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		1		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		4		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$		0.83	1.2	V

Package Dimensions

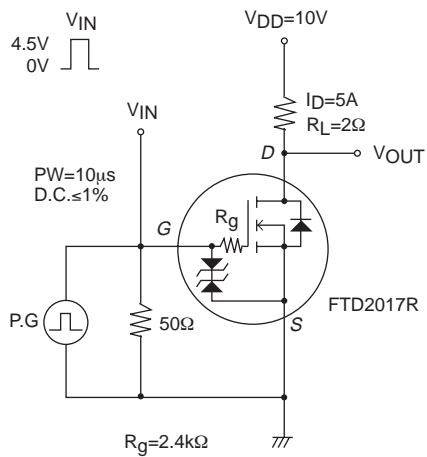
unit : mm (typ)
7006A-005



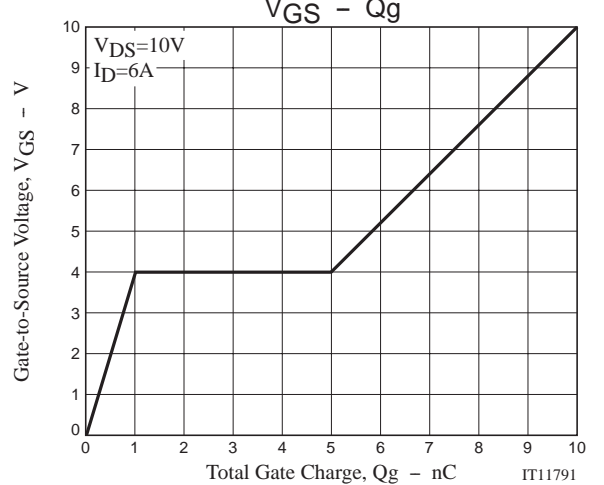
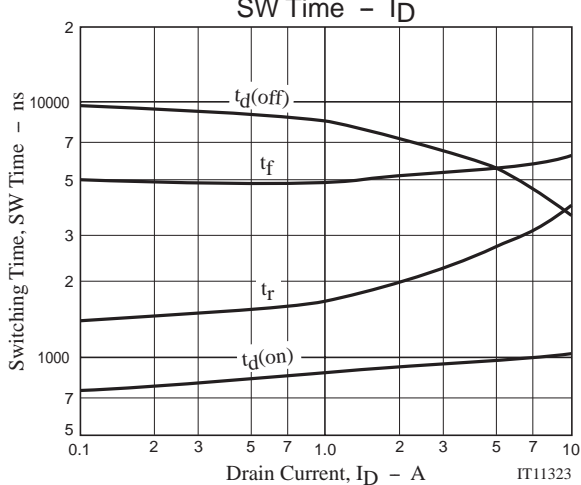
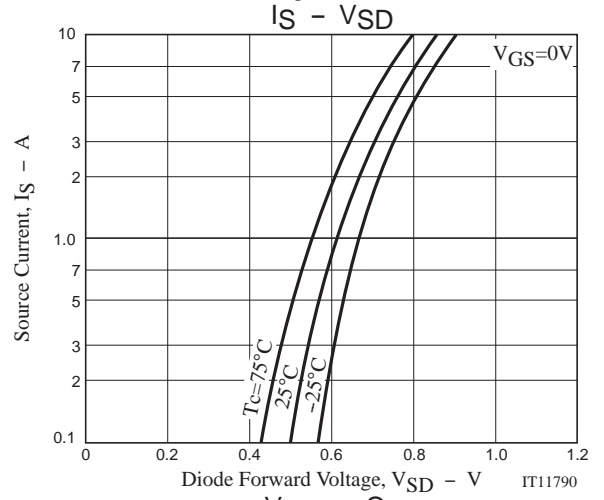
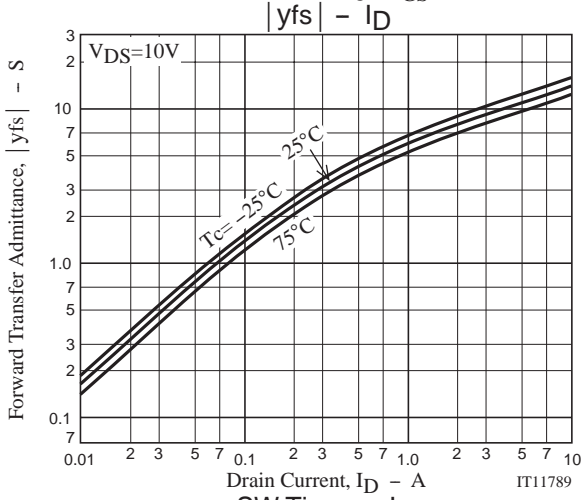
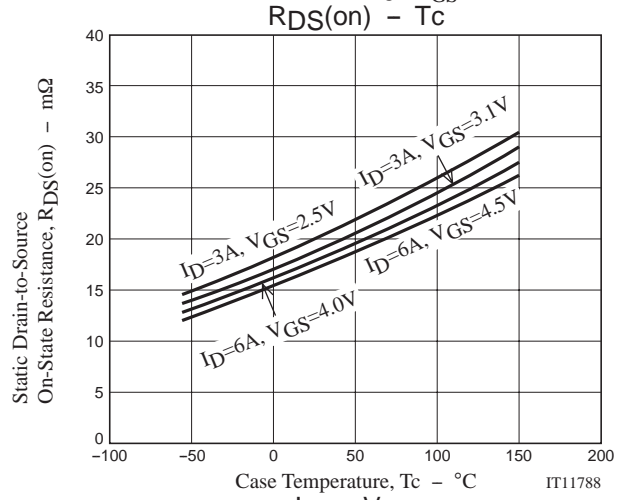
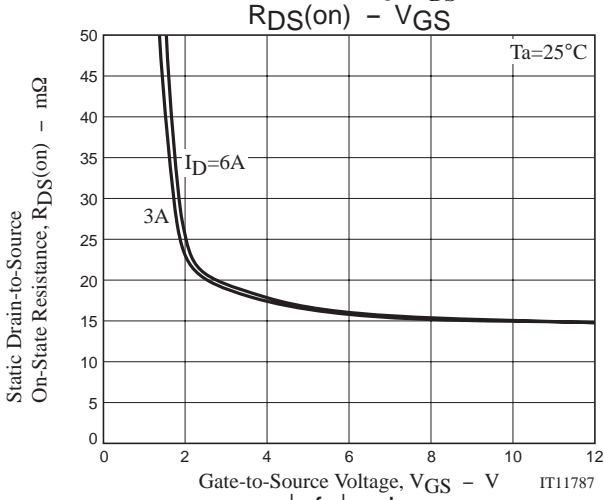
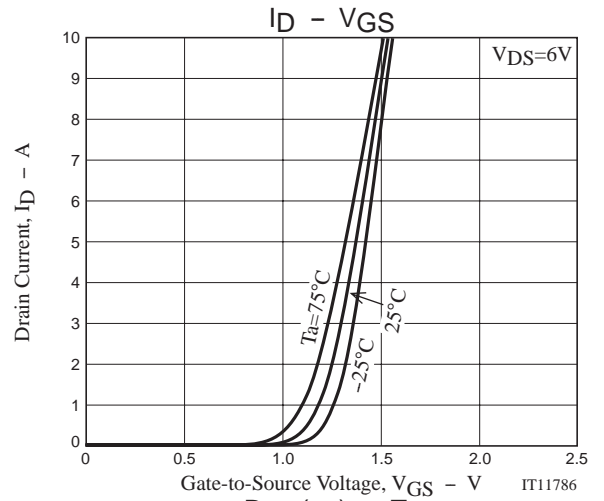
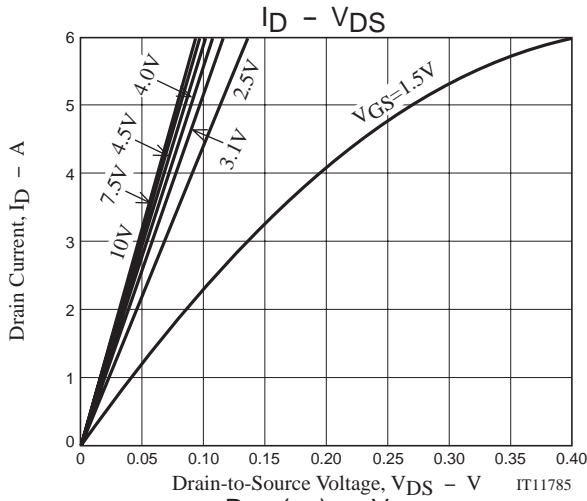
Electrical Connection



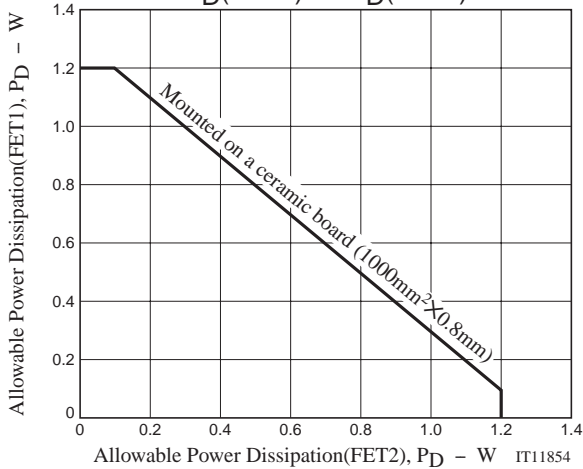
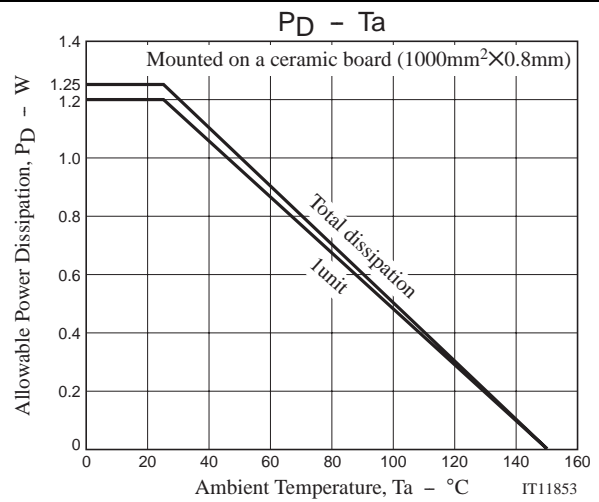
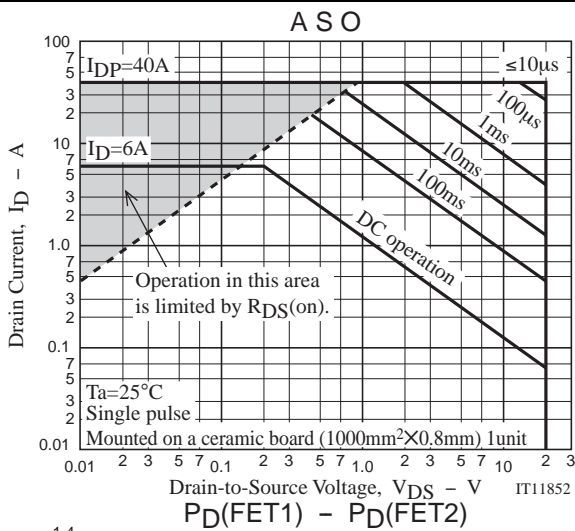
Switching Time Test Circuit



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Note on usage : Since the FTD2017R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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